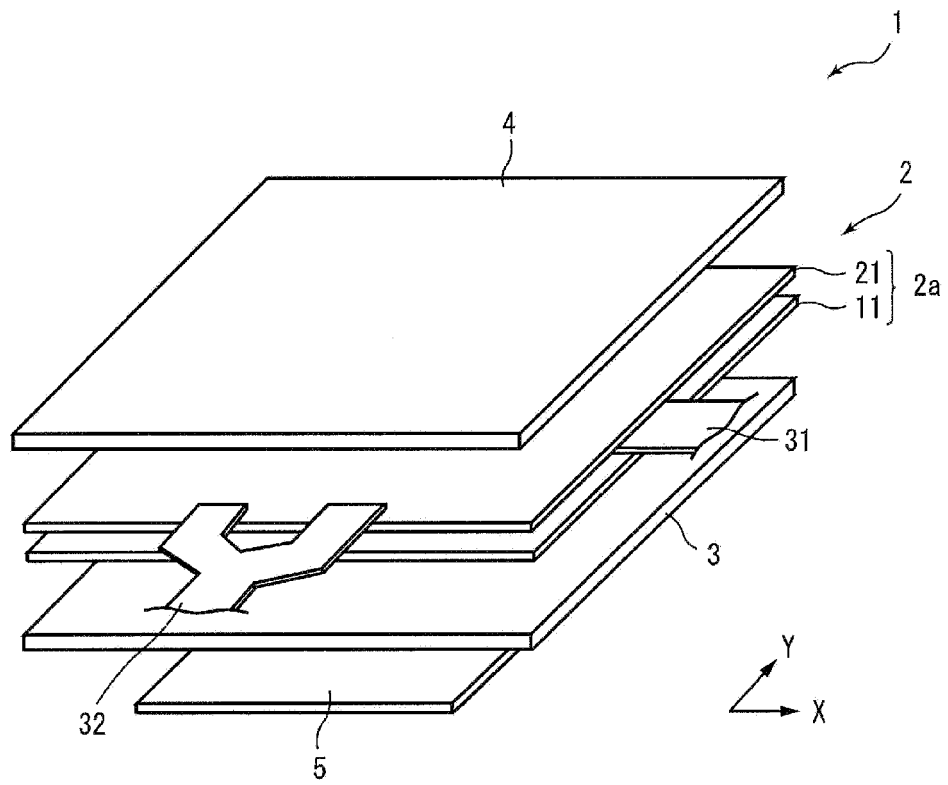
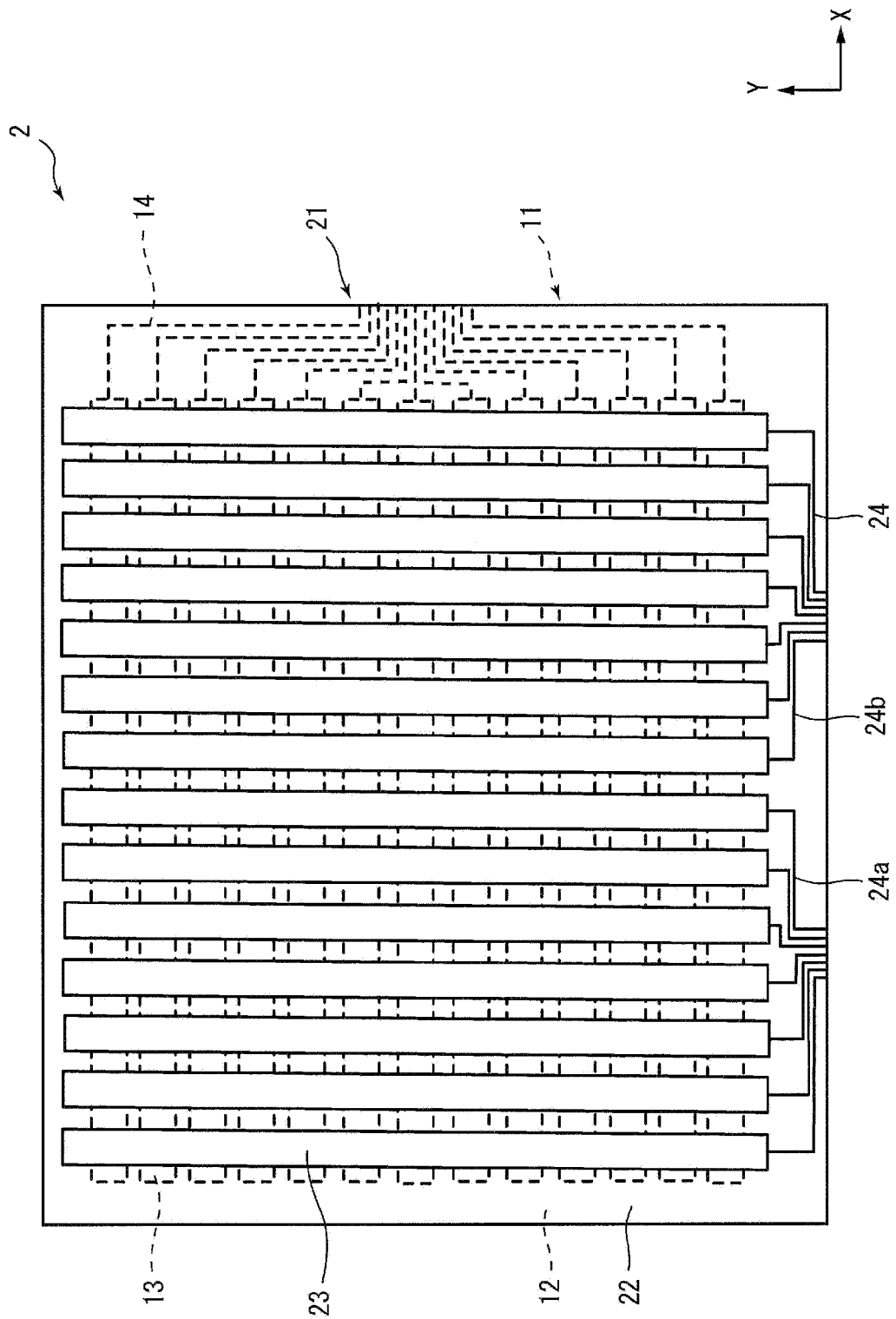


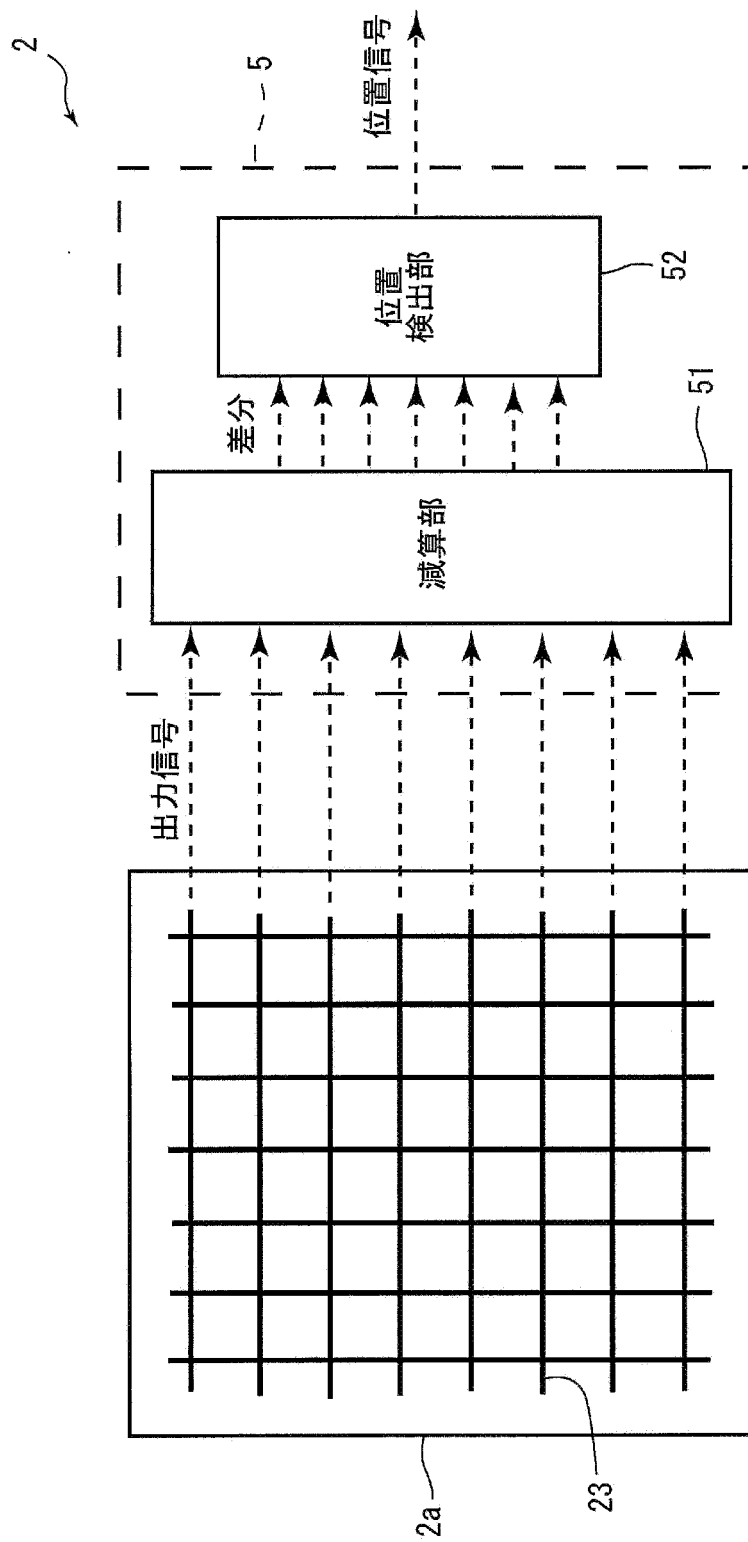
[図1]



[図2]

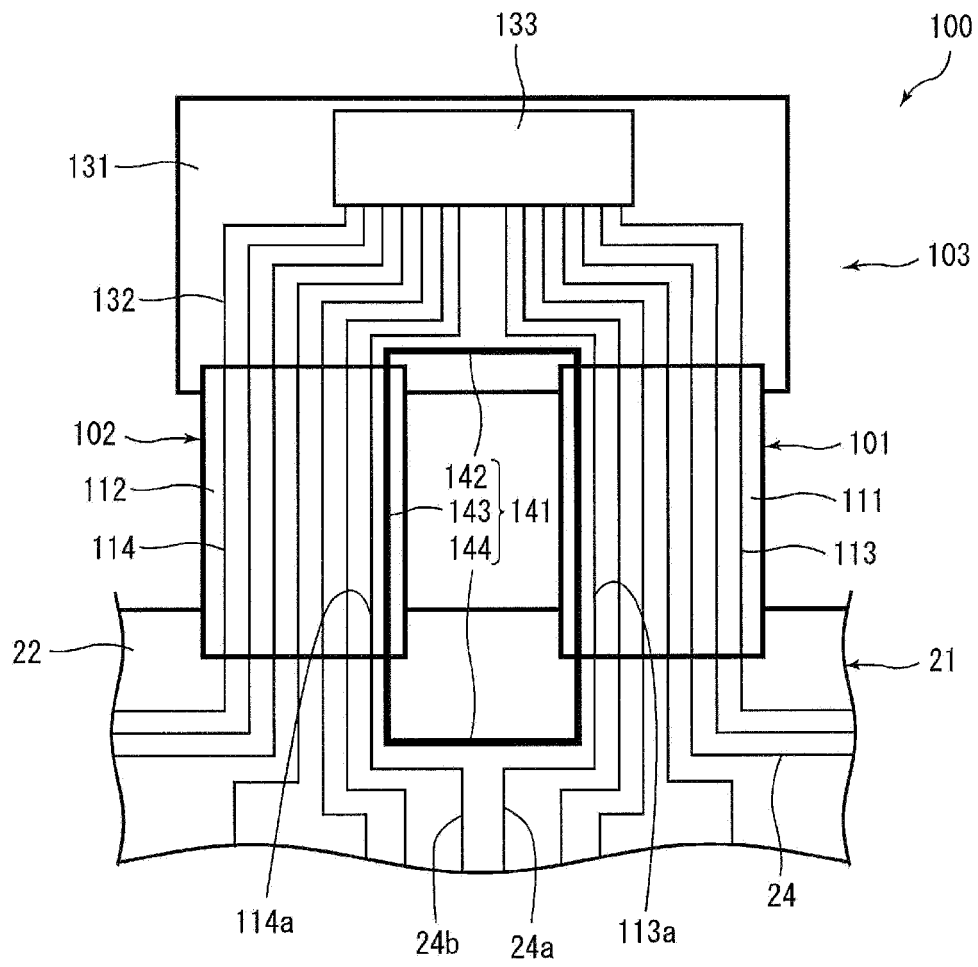


[図3]

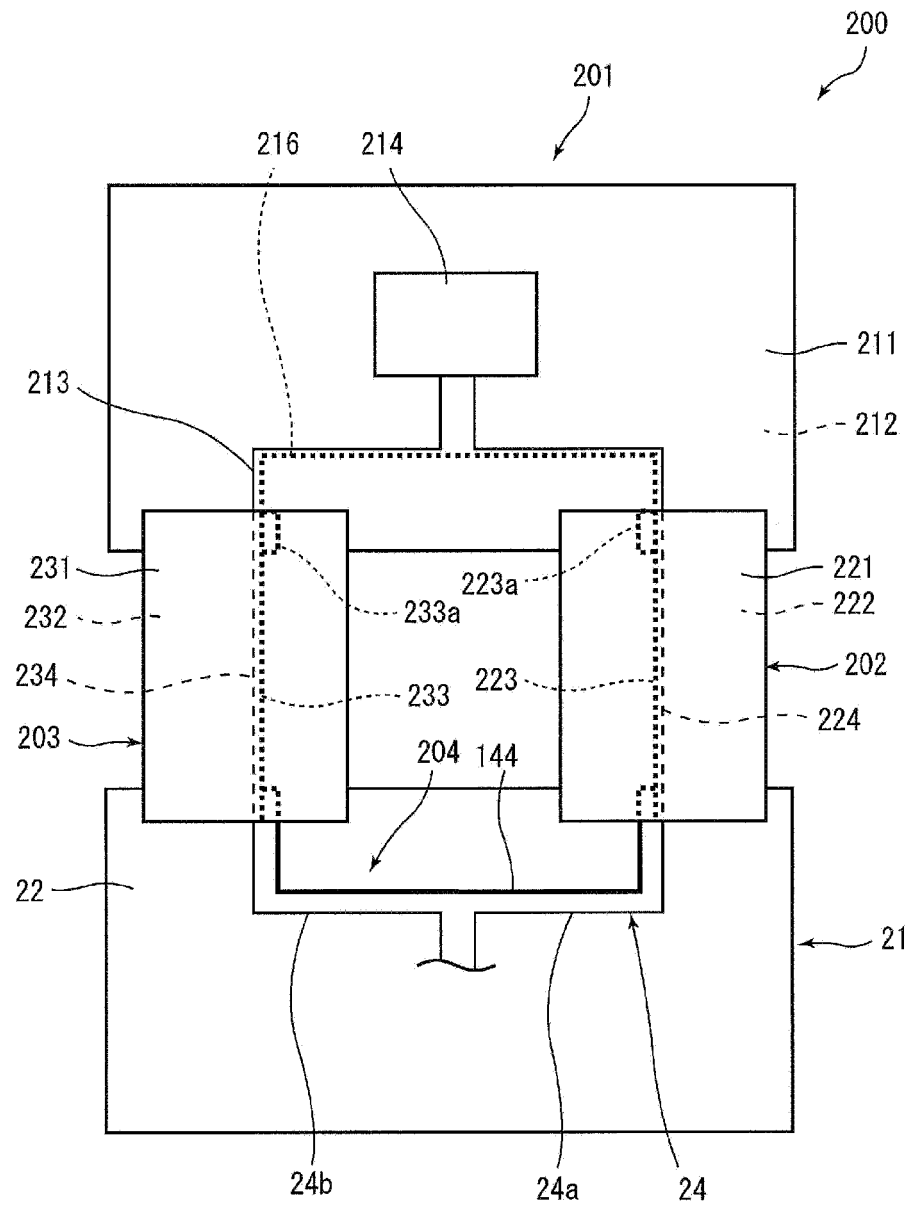


A cross-sectional view of a semiconductor device. A central pentagonal cavity is formed within a substrate. The cavity is defined by a thick layer 61, which consists of an inner layer 62 and an outer layer 63. The cavity is open at the top and bottom. The top opening is defined by a structure 34a, and the bottom opening is defined by a structure 34b. The side walls of the cavity are labeled 24a and 24b. A lightning bolt symbol is shown to the right of the cavity, indicating a high-voltage or high-temperature process.

[図6]

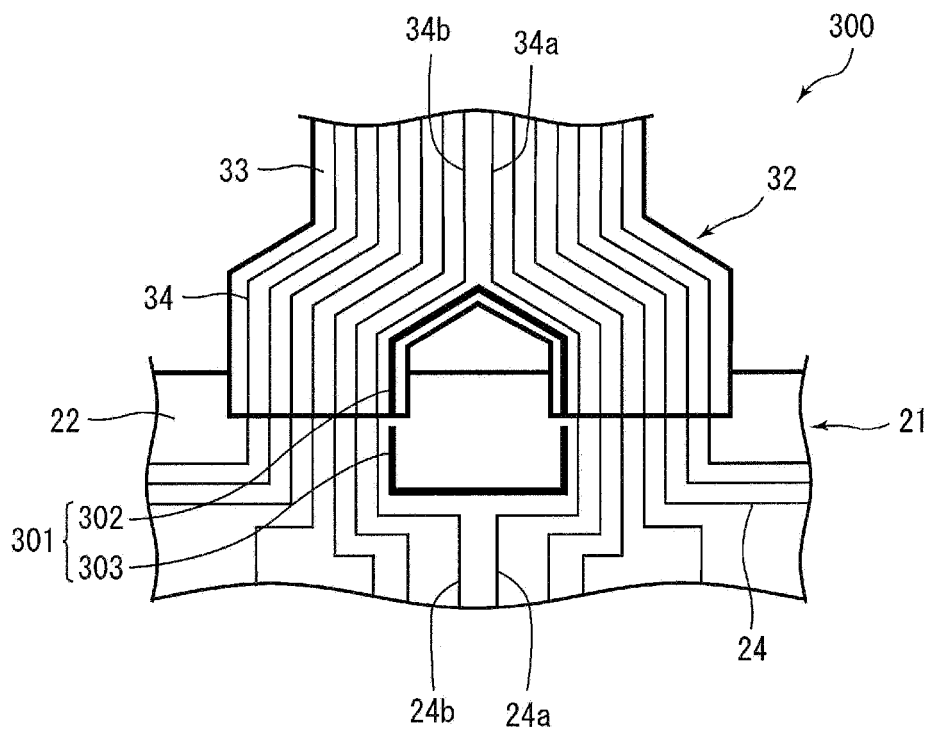


[図7]





[図9]



[図10]

